

ABSTRACT OF THE DISCLOSURE

In a solid-state image pickup device, third transfer electrodes are disposed in parallel to vertical transfer registers, and second transfer electrodes are disposed vertically to the vertical transfer registers. These transfer electrodes are also formed on the read-out gate portions to supply a driving voltage for reading out signal charges from photoelectric conversion elements. On the basis of the driving voltage applied to both the third and second transfer electrodes, the read-out of the signal charges to the vertical transfer registers is carried out. At the portion where the read-out of the signal charges is carried out, the transfer electrode at the read-out gate portion side and the sensor area of the photoelectric conversion element are formed so as to be adjacent to each other. At the portion where no read-out of signal charges is carried out, an offset area is provided between the transfer electrode at the read-out gate portion side and the sensor area of the photoelectric conversion element.